課題番号 :F-19-KT-0107

利用形態:機器利用

利用課題名(日本語) :(100)単結晶シリコンを用いた同調型振動リングジャイロスコープにおける形状補償

Program Title(English) : Geometrical Compensation for Mode-Matching of (100) Silicon Ring Resonator for

Vibratory Gyroscope

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#### 1. 概要(Summary)

A vibratory ring gyroscope (VRG) with nonuniform radial width to compensate the elastic anisotropy of (100) SCS was introduced and characterized by the finite element analysis (FEA) simulation and experiments [1]. Moreover, the effect of suspending beams of a VRG on  $\Delta f$  was also analyzed and their dimensions were optimized to achieve minimal  $\Delta f$  of 9Hz in simulation which was mode-matched. With this nearly proposed geometrical compensation, a VRG was fabricated by standard SOI fabrication process using a (100) SCS wafer with a 22-µm-thick device layer. In the frequency response test, the compensated VRG  $\Delta f$ shown a smaller 126 Hz, than uncompensated one with uninform radial width, 189 Hz.

# 2. <u>実験(Experimental)</u>

### 【利用した主な装置】

[A03] Laser Pattern Generator, [A05] HighPrecision Double-Sided Mask Aligner, [B08-1]Deep Reactive Ion Etching machine

## 【実験方法】

The compensated and uncompensated VRGs were both fabricated on (100) silicon-on insulator (SOI) wafers of a 22-µm-thick device layer. Firstly, the ring and suspending beams were patterned using ultraviolet (UV) lithography (Mask aligner, MA6 BSA, SUSS MicroTec) and deep reactive-ion etching (DRIE) (RIE-800iPB-KU, Samco). After photoresist removal, the 7-µm-thick negative photoresist

(PMER P-WG300, Tokyo Ohka Kogyo) was spin-coated and electrode pads were patterned by UV lithography (Mask aligner, PEM-800, Union Optical). Then the aluminum layer of 200 nm thickness was deposited by electron beam deposition (EB1200, Canon). And Lift off process with n-methyl-2-pyrrolidone (NMP) was used to pattern the aluminum electrode pads. Finally, the 2-μm-thick sacrificial layer was etched by vapor hydrofluoric acid (MLT-SLE-0x, Sumitomo Precision Products) and the structures of ring and suspending beams were released.

## 3. 結果と考察(Results and Discussion)

A fabricated device chip is also shown in Fig. 1.

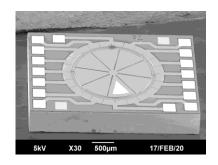


Fig. 1 Device image of a VRG.

## 4. その他・特記事項(Others)

## •参考文献

[1] Hopcroft M. A. et al., J. Microelectromech. Syst., 2010, 19(2): 229-238.

## 5. 論文·学会発表(Publication/Presentation)

(1) S. Yunyi, Y. Hirai, and T. Tsuchiya. The 7<sup>th</sup> IEEE International Symposium on Inertial Sensor & Systems (INERTIAL 2020), Hiroshima, Japan 6. 関連特許(Patent) なし